



AO4490

30V N-Channel MOSFET

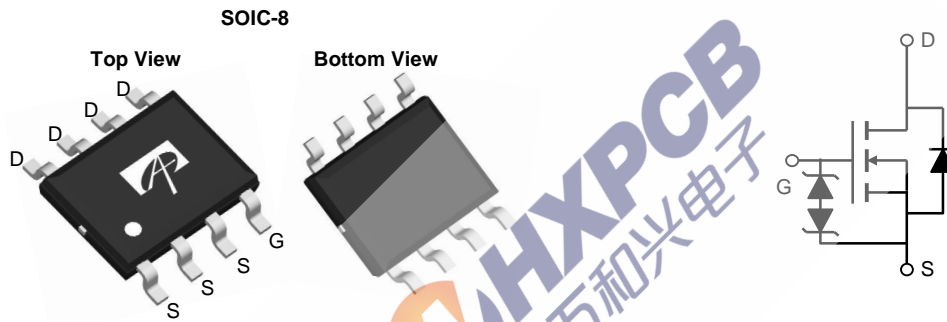
General Description

The AO4490 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V, while retaining a 20V $V_{GS(MAX)}$ rating. It is ESD protected. This device is suitable for use as a load switch and general purpose applications.

Product Summary

V_{DS} (V) = 30V
 I_D = 16A (V_{GS} = 10V)
 $R_{DS(ON)} < 7.2m\Omega$ (V_{GS} = 10V)
 $R_{DS(ON)} < 10m\Omega$ (V_{GS} = 4.5V)

ESD Protected
 100% UIS Tested
 100% Rg Tested



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^{AF}	$T_A=25^\circ\text{C}$	16	A
	$T_A=70^\circ\text{C}$	13	
Pulsed Drain Current ^B	I_{DM}	120	
Avalanche Current ^G	I_{AR}	30	A
Repetitive avalanche energy $L=0.3mH$ ^G	E_{AR}	135	mJ
Power Dissipation	$T_A=25^\circ\text{C}$	2.8	W
	$T_A=70^\circ\text{C}$	1.8	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	32	45	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A		Steady-State	62	75
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	18	24	$^\circ\text{C/W}$

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	30	37		V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=30\text{V}$, $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			1 5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 16\text{V}$			10	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	1.4	1.8	2.5	V
$I_{D(ON)}$	On state drain current	$V_{GS}=10\text{V}$, $V_{DS}=5\text{V}$	120			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$, $I_D=16\text{A}$ $T_J=125^\circ\text{C}$		6 8.5	7.2 10	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}$, $I_D=12\text{A}$		8	10	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}$, $I_D=16\text{A}$		55		S
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}$, $V_{GS}=0\text{V}$		0.70	1.0	V
I_S	Maximum Body-Diode Continuous Current				4	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=15\text{V}$, $f=1\text{MHz}$		1803	2170	pF
C_{oss}	Output Capacitance			387		pF
C_{rss}	Reverse Transfer Capacitance			238		pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		1.3	2	Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $I_D=16\text{A}$		36	48	nC
$Q_g(4.5\text{V})$	Total Gate Charge			19		nC
Q_{gs}	Gate Source Charge			3.9		nC
Q_{gd}	Gate Drain Charge			8.7		nC
$t_{D(on)}$	Turn-On DelayTime			7.6		ns
t_r	Turn-On Rise Time	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $R_L=1\Omega$, $R_{GEN}=3\Omega$		6.4		ns
$t_{D(off)}$	Turn-Off DelayTime			27		ns
t_f	Turn-Off Fall Time			8.5		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=16\text{A}$, $di/dt=100\text{A}/\mu\text{s}$		27	33	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=16\text{A}$, $di/dt=100\text{A}/\mu\text{s}$		17		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using $<300\mu\text{s}$ pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

F: The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.

G: EAR and IAR ratings are based on low frequency and duty cycles such that $T_J(\text{start})=25^\circ\text{C}$ for each pulse.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

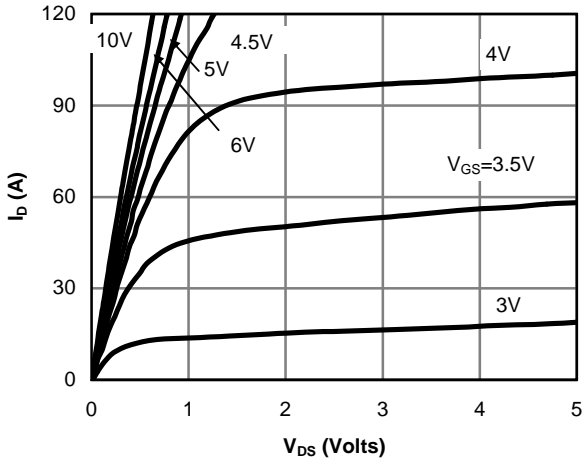


Figure 1: On-Region Characteristics

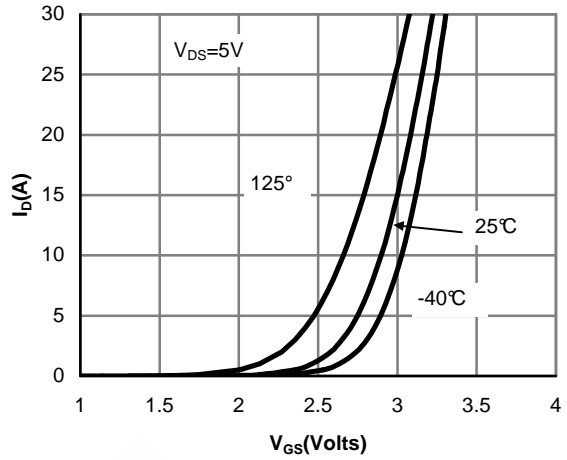


Figure 2: Transfer Characteristics

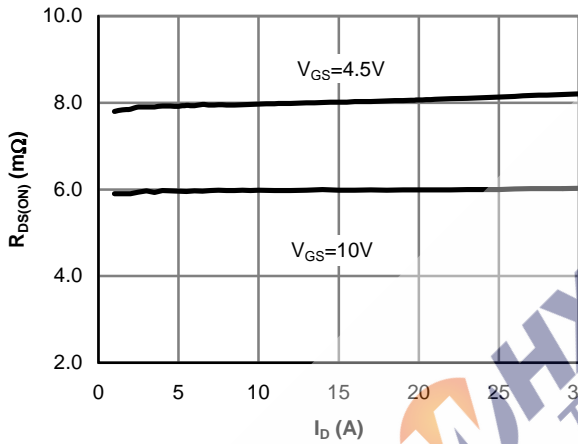


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

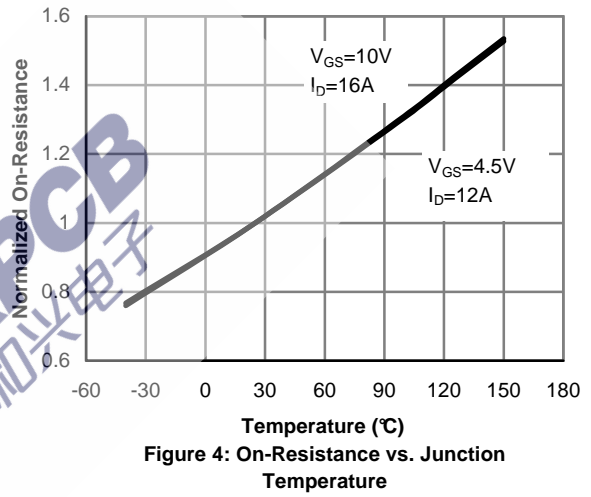


Figure 4: On-Resistance vs. Junction Temperature

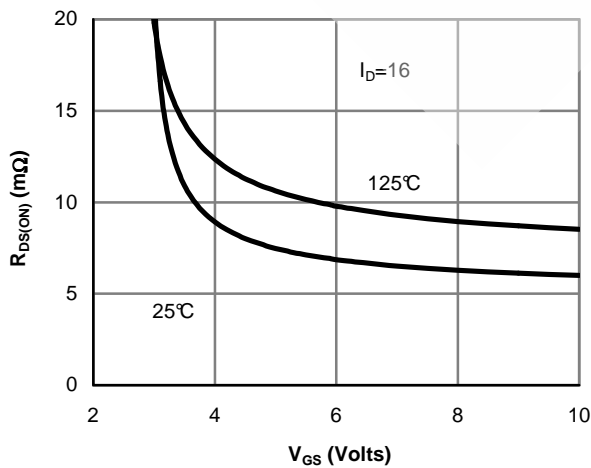


Figure 5: On-Resistance vs. Gate-Source Voltage

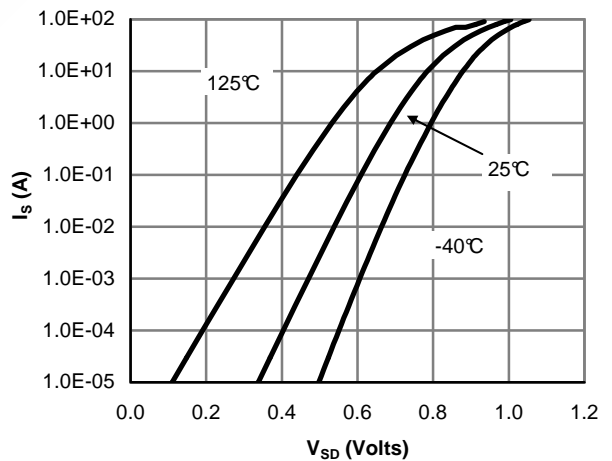


Figure 6: Body-Diode Characteristics

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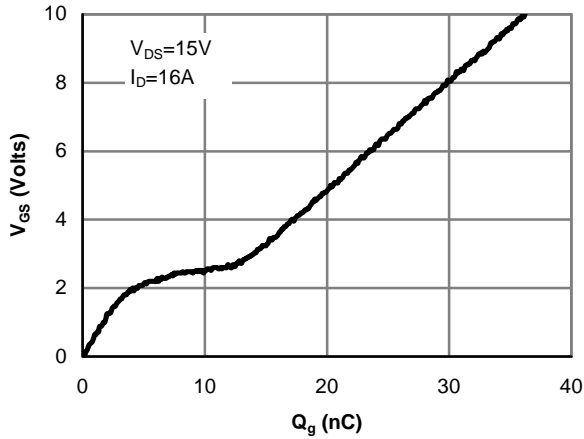


Figure 7: Gate-Charge Characteristics

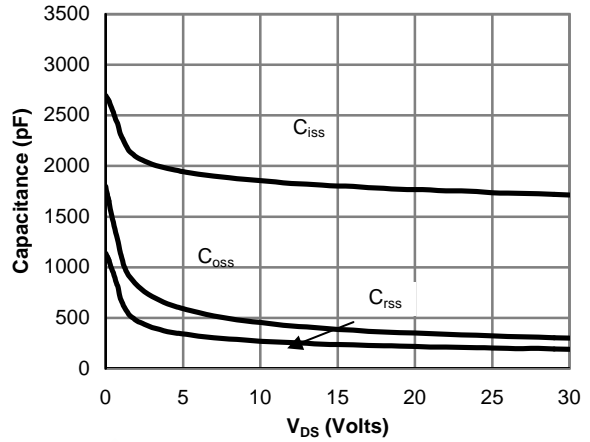


Figure 8: Capacitance Characteristics

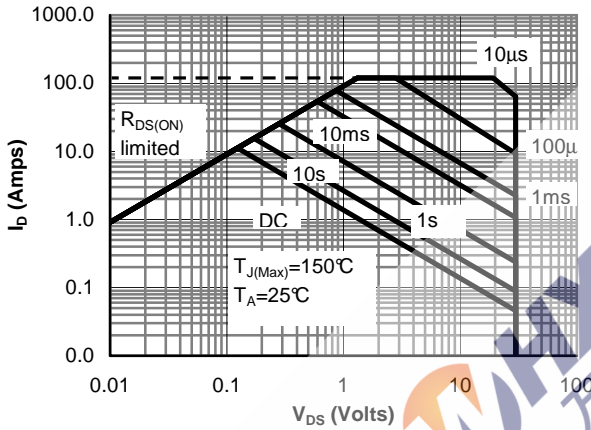


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

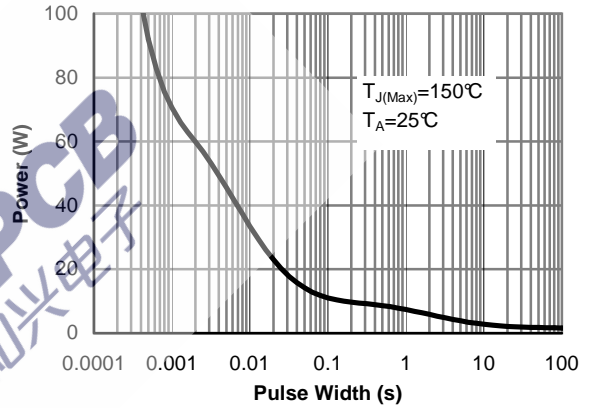


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

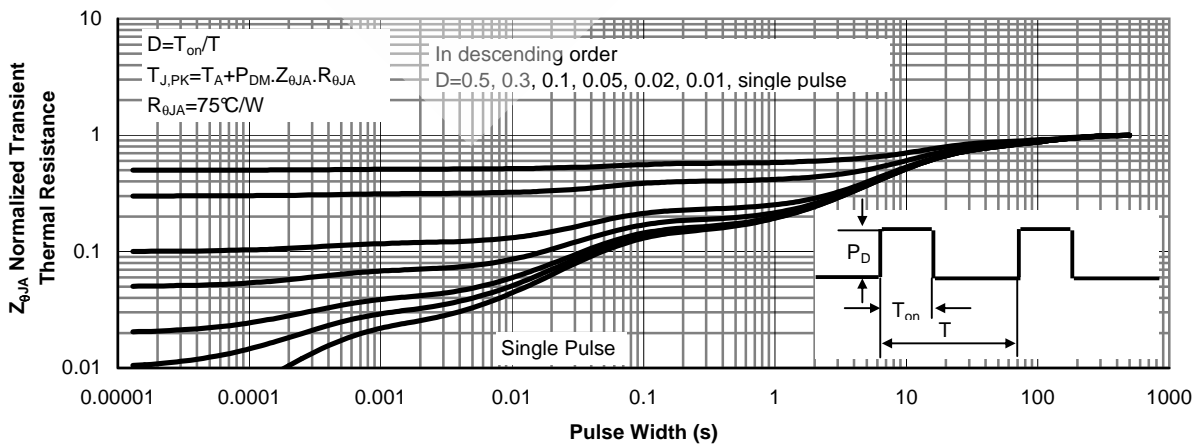


Figure 11: Normalized Maximum Transient Thermal Impedance(Note E)

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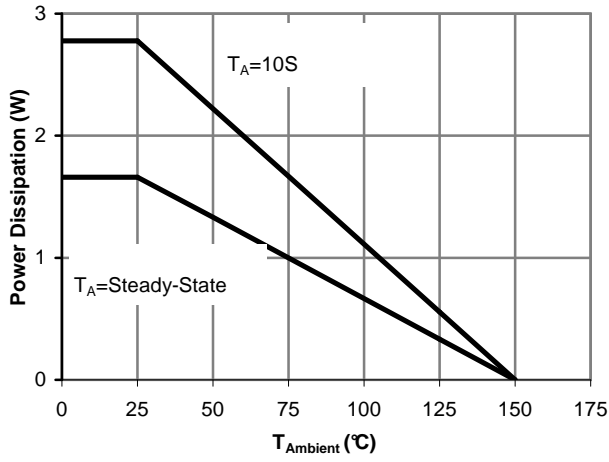
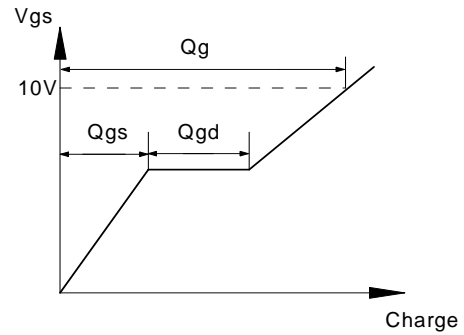
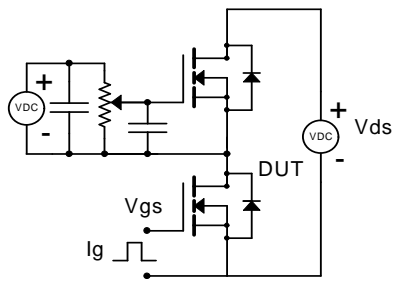


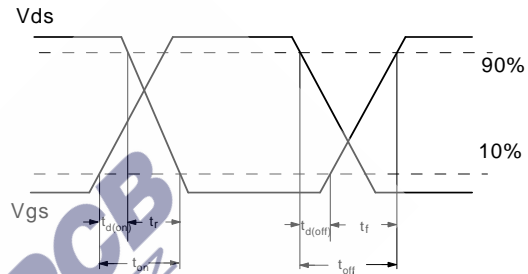
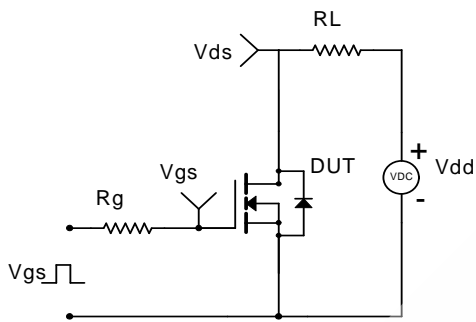
Figure 12: Power De-rating (Note A)



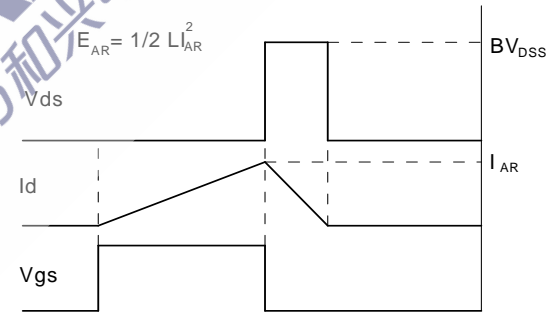
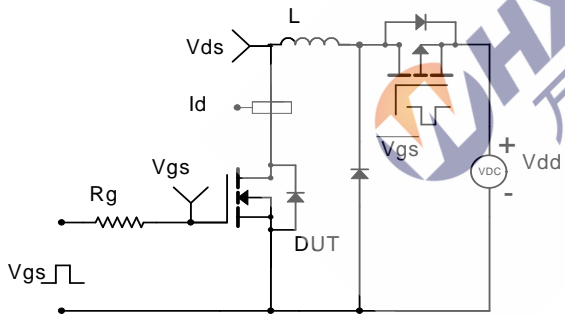
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

